

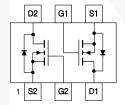
January 2015

2N7002DW N-Channel Enhancement Mode Field Effect Transistor

Features

- Dual N-Channel MOSFET
- · Low On-Resistance
- · Low Gate Threshold Voltage
- · Low Input Capacitance
- · Fast Switching Speed
- · Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- · Lead Free/RoHS Compliant





Ordering Information

Part Number	Top Mark	Package	Packing Method	
2N7002DW	2N	2N SC70 6L Tape		

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter		Value	Unit
V_{DSS}	Drain-Source Voltage		60	V
V_{DGR}	Drain-Gate Voltage (R _{GS} ≤ 1.0 MΩ)		60	V
V _{GSS}	Gate-Source Voltage	Continuous	±20	V
		Pulsed	±40	
I _D D	Drain Current	Continuous	115	
		Continuous at 100°C	73	mA
		Pulsed	800	
T _J , T _{STG}	Junction and Storage Temperature Range		-55 to +150	°C

Thermal Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Value	Unit
D	Total Device Dissipation	200	mW
P _D	Derate Above T _A = 25°C	1.6	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient ⁽¹⁾	625	°C/W

Note:

1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

Electrical Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Charact	eristics ⁽²⁾					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V, } I_D = 10 \mu\text{A}$	60	78		V
I _{DSS}		V _{DS} = 60 V, V _{GS} = 0 V		0.001	1.0	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125°C		7	500	
I _{GSS}	Gate-Body Leakage	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$		0.2	±10	nA
On Characte	eristics ⁽²⁾		•			
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1.00	1.76	2.00	V
	Static Drain-Source On-Resistance	$V_{GS} = 5 \text{ V}, I_D = 0.05 \text{ A}$		1.6	7.5	Ω
R _{DS(ON)}		V _{GS} = 10 V, I _D = 0.5 A			2.0	
		V_{GS} = 10 V, I_{D} = 0.5 A, T_{J} = 125°C		2.53	13.5	
I _{D(ON)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 7.5 V	0.50	1.43		Α
9 _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 0.2 A	80.0	356.5		mS
Dynamic Ch	naracteristics					
C _{iss}	Input Capacitance	.,	<i>//</i>	37.8	50	pF
C _{oss}	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		12.4	25	pF
C _{rss}	Reverse Transfer Capacitance	1.32		6.5	7	pF
	Characteristics					
t _{D(ON)}	Turn-On Delay Time $V_{DD} = 30 \text{ V}, I_D = 0.2 \text{ A},$			5.85	20	ns
t _{D(OFF)}	Turn-Off Delay Time	V_{GEN} = 10 V, R _L = 150 Ω, R _{GEN} = 25 Ω		12.5	20	ns

Note:

2. Short duration test pulse used to minimize self-heating effect.

Typical Performance Characteristics

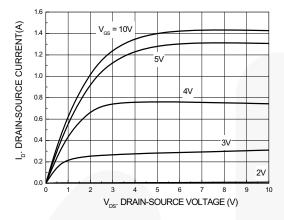


Figure 1. On-Region Characteristics

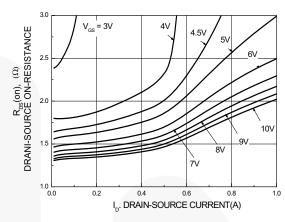


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

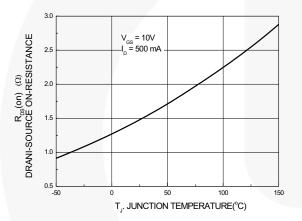


Figure 3. On-Resistance Variation with Temperature

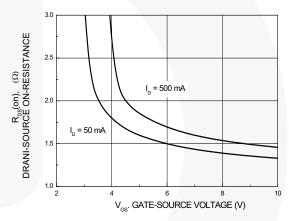


Figure 4. On-Resistance Variation with Gate-Source Voltage

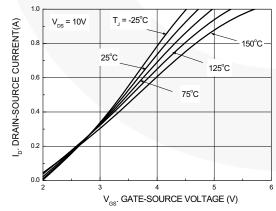


Figure 5. Transfer Characteristics

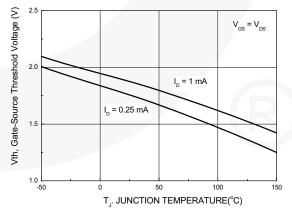


Figure 6. Gate Threshold Variation with Temperature

Typical Performance Characteristics (Continued)

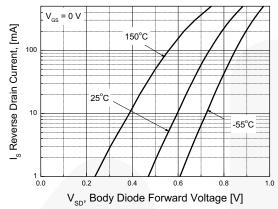


Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature

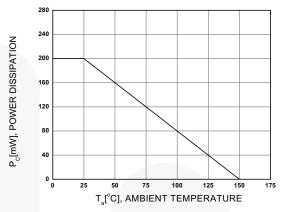


Figure 8. Power Derating

Physical Dimensions

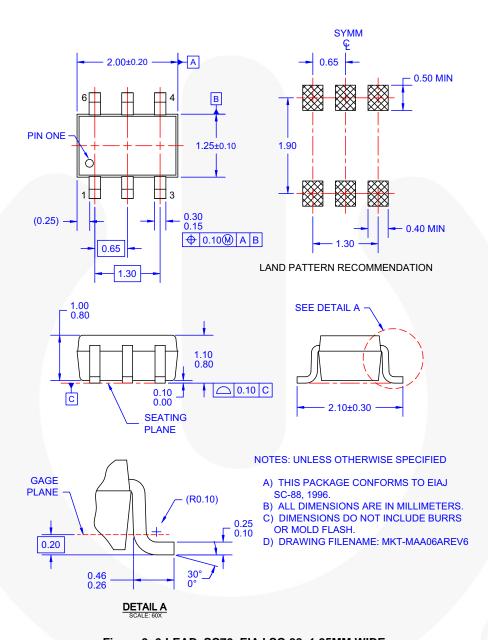


Figure 9. 6-LEAD, SC70, EIAJ SC-88, 1.25MM WIDE





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